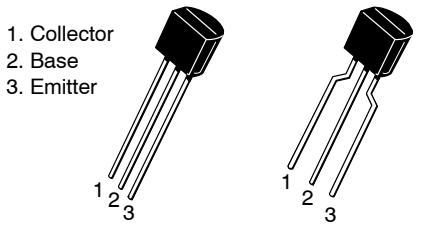
PNP Epitaxial Silicon Transistor

BC327



TO−92 3
CASE 135AN

TO−92 3 LF
CASE 135AR

Features

- Switching and Amplifier Applications
- Suitable for AF−Driver Stages and Low−Power Output Stages
- Complement to BC337/BC338
- These are Pb−Free Devices

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V_{CES}	Collector−Emitter Voltage	−50	V
V_{CEO}	Collector−Emitter Voltage	−45	V
V_{EBO}	Emitter−Base Voltage	−5	V
I_C	Collector Current (DC)	−800	mA
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted.) (Note 1)

Symbol	Characteristic	Value	Unit
P_D	Power Dissipation Derate Above 25°C	625 5.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

1. PCB size: FR−4, 76 mm × 114 mm × 1.57 mm (3.0 inch × 4.5 inch × 0.062 inch) with minimum land pattern size.

MARKING DIAGRAM

A = Assembly Location
BC327xx = Specific Device Code
xx = 25, 40
Y = Year
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
BC327BU	TO−92 3 (Pb−Free)	10,000 Units / BLKBG
BC32740BU	TO−92 3 (Pb−Free)	10,000 Units / BLKBG
BC32725BU	TO−92 3 (Pb−Free)	10,000 Units / BLKBG
BC32725TA	TO−92 3 LF (Pb−Free)	2,000 Units / FNFLD
BC32740TA	TO−92 3 LF (Pb−Free)	2,000 Units / FNFLD

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV_{CEO}	Collector−Emitter Breakdown Voltage	I_C = −10 mA, I_B = 0	−45	–	–	V
BV_{CES}	Collector−Emitter Breakdown Voltage	I_C = −0.1 mA, V_{BE} = 0	−50	–	–	V
BV_{EBO}	Emitter−Base Breakdown Voltage	I_E = −10 μA, I_C = 0	−5	–	–	V
I_{CES}	Collector Cut−Off Current	V_{CE} = −45 V, I_B = 0	–	−2	−100	nA
h_{FE1}	DC Current Gain	V_{CE} = −1 V, I_C = −100 mA	100	–	630	
h_{FE2}		V_{CE} = −1 V, I_C = −300 mA	60	–		
V_{CE}(sat)	Collector−Emitter Saturation Voltage	I_C = −500 mA, I_B = −50 mA	–	–	−0.7	V
V_{BE}(on)	Base−Emitter On Voltage	V_{CE} = −1 V, I_C = −300 mA	–	–	−1.2	V
f_T	Current Gain Bandwidth Product	V_{CE} = −5 V, I_C = −10 mA, f = 20 MHz	–	100	–	MHz
C_{ob}	Output Capacitance	V_{CB} = −10 V, I_E = 0, f = 1 MHz	–	12	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} Classification

Classification	16	25	40
h_{FE1}	100 ~ 250	160 ~ 400	250 ~ 630
h_{FE2}	60 ~	100 ~	170 ~

TYPICAL CHARACTERISTICS

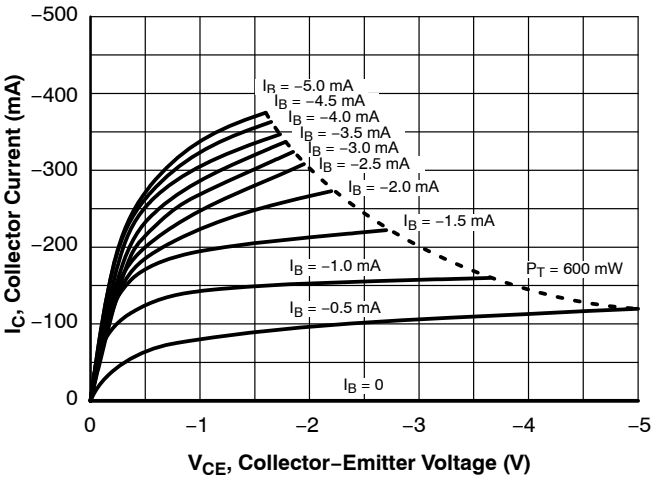


Figure 1. Static Characteristic

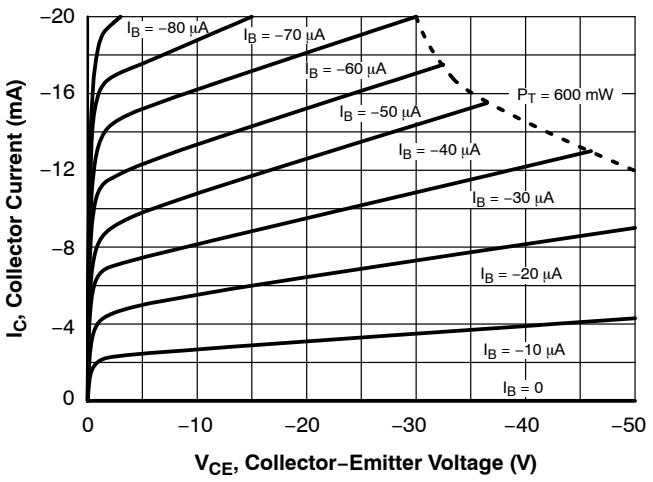


Figure 2. Static Characteristic

TYPICAL CHARACTERISTICS (Continued)

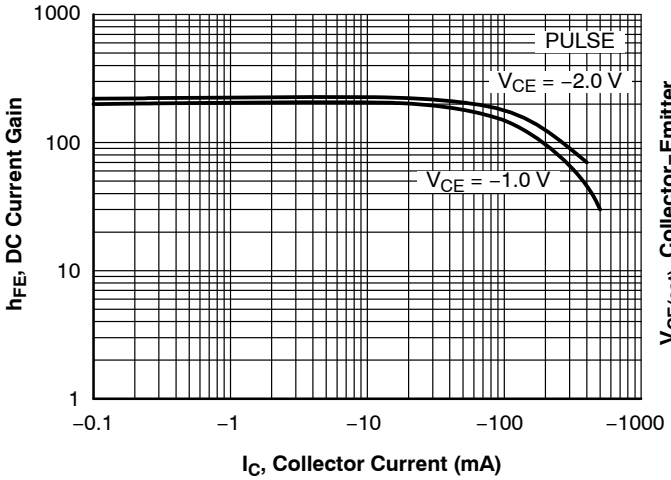


Figure 3. DC Current Gain

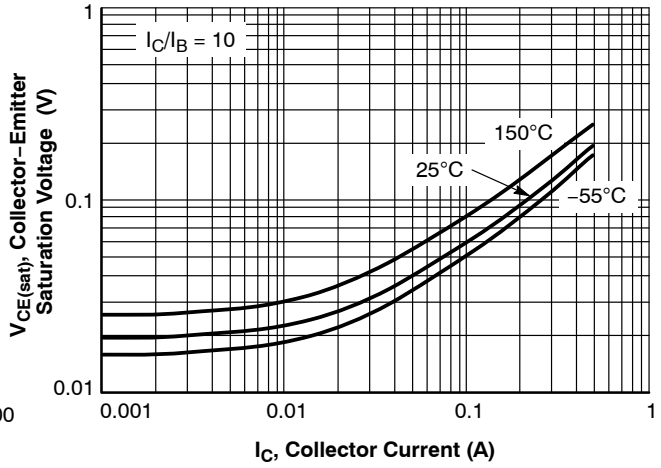


Figure 4. Collector−Emitter Saturation Voltage vs. Collector Current

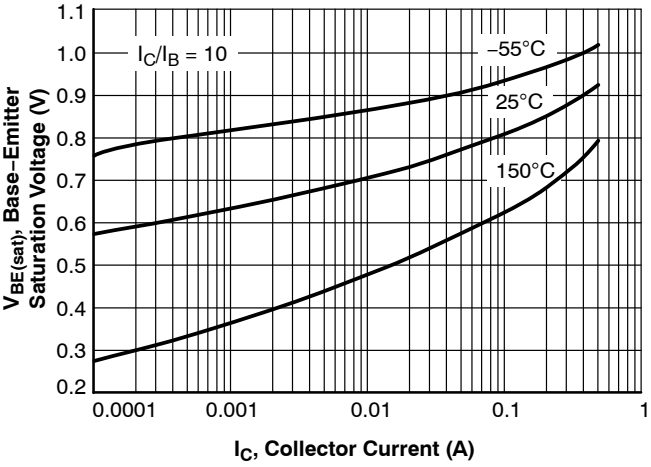


Figure 5. Base Emitter Saturation Voltage vs. Collector Current

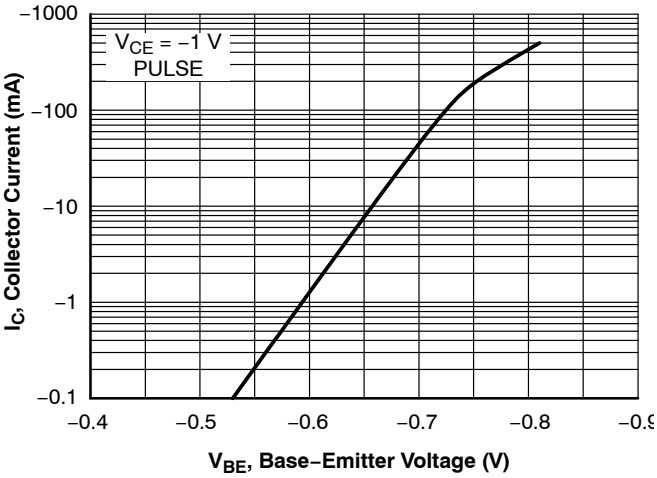


Figure 6. Base−Emitter On Voltage

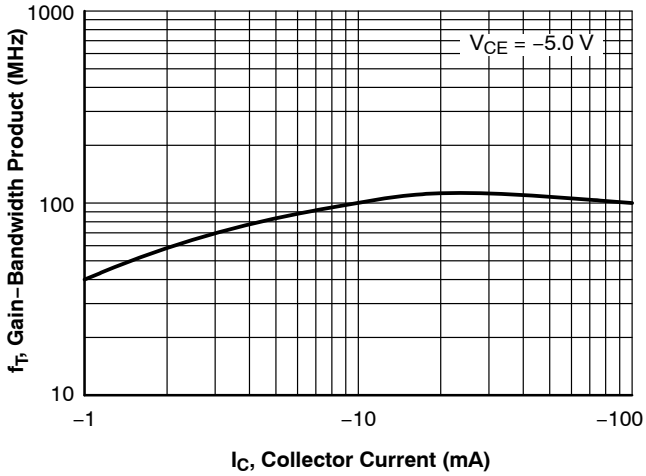


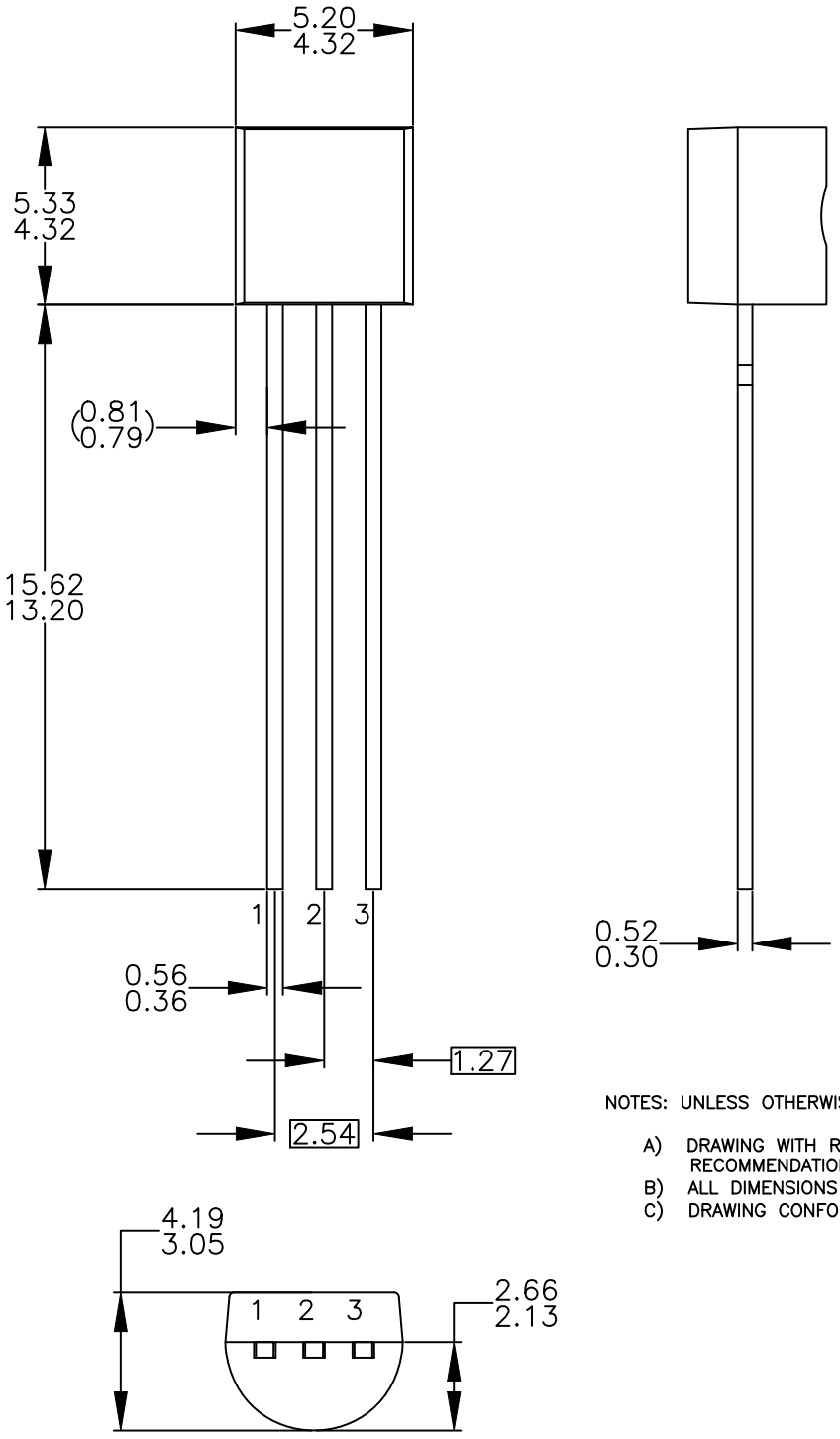
Figure 7. Gain Bandwidth Product

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

TO−92 3 4.825x4.76
CASE 135AN
ISSUE O

DATE 31 JUL 2016



NOTES: UNLESS OTHERWISE SPECIFIED

A) DRAWING WITH REFERENCE TO JEDEC TO−92 RECOMMENDATIONS.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DRAWING CONFORMS TO ASME Y14.5M−2009.

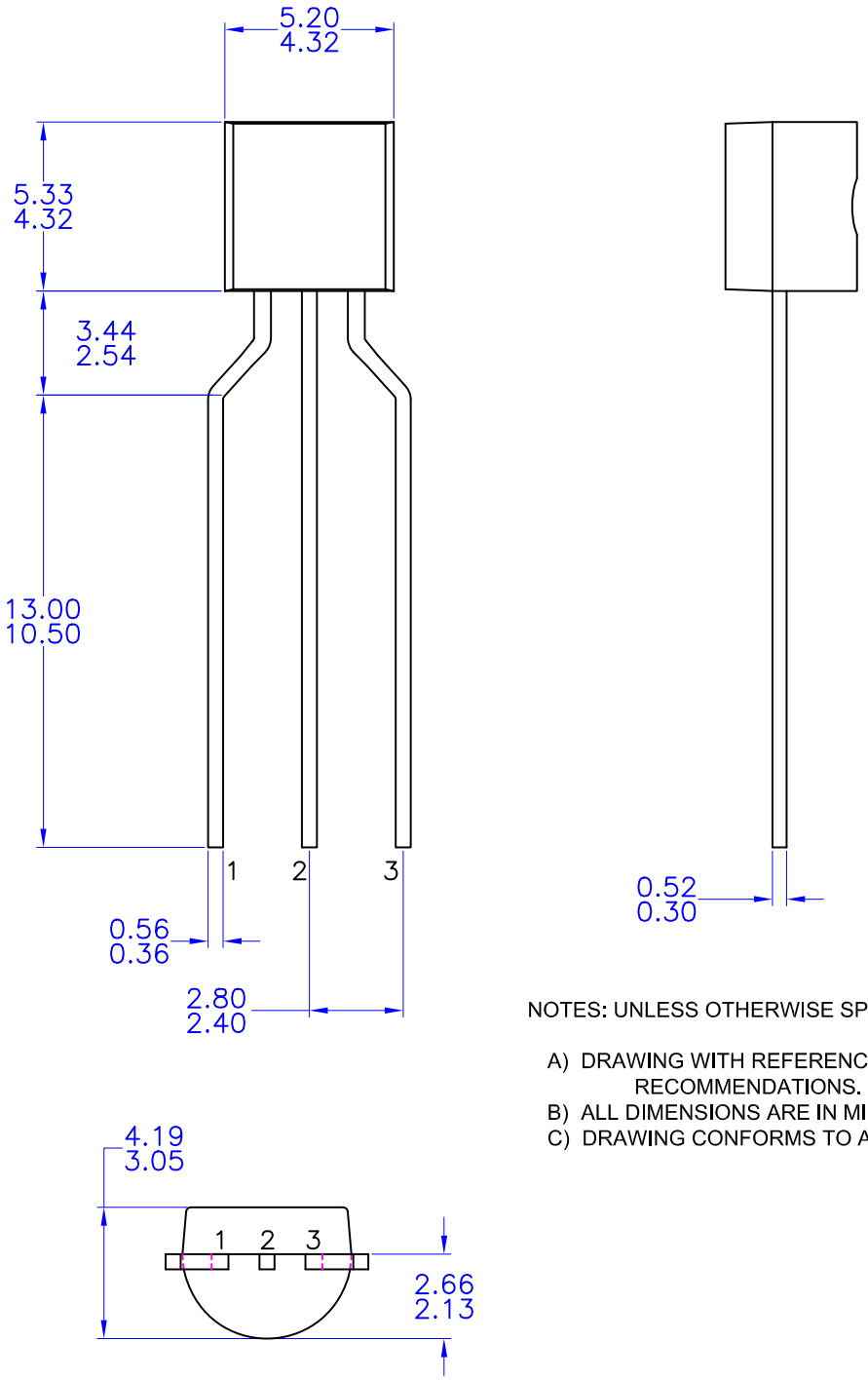
DOCUMENT NUMBER:	**98AON13880G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**TO−92 3 4.825X4.76**	**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

TO−92 3 4.83x4.76 LEADFORMED
CASE 135AR
ISSUE O

DATE 30 SEP 2016



NOTES: UNLESS OTHERWISE SPECIFIED

A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DRAWING CONFORMS TO ASME Y14.5M-1994

DOCUMENT NUMBER:	**98AON13879G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**TO−92 3 4.83X4.76 LEADFORMED**		**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales